Product Overview

NSVF6003SB6: RF Transistor, NPN Single, 12 V, 150 mA, f_T = 7 GHz

For complete documentation, see the data sheet.

This RF transistor is designed for low noise amplifier applications. CPH package is suitable for use under high temperature environment because it has superior heat radiation characteristics. This RF transistor is AEC-Q101 qualified and PPAP capable for automotive applications.

Features

- AEC-Q101 qualified and PPAP capable
- Pb-Free, Halogen Free and RoHS compliance
- High Current (IC = 150 mA)
- Ultra miniature and thin 6 pin package
- Large Collector Dissipation (800 mW)
- High Gain (fT = 7 GHz typ)

Benefits

- Suitable for automotive applications
- Environmental consideration
- Realize a low distorted characteristic
- Superior heat radiation characteristics
- Enable movement under the high temperature environment

Applications

- Low Noise Amplifier

End Products

- Car FM Radio
- TV for Automotive

Part Electrical Specifications

Product	Compliance	Status	Polarity	I_C Continuous (A)	$V_{CEO(sus)}$ Min (V)	h_{FE} Min	h_{FE} Max	P_{TM} Max (W)	f_T Min (MHz)	NF Typ. (dB)	|S21e| 2 Typ. (dB)	Package Type
NSVF6003SB6T1G	AEC Qualified PPAP Capable Pb-free Halide free	Active	NPN	0.15	12	100	180	0.8	7000	1.8	9	CPH-6

For more information please contact your local sales support at www.onsemi.com.

Created on: 3/1/2018